MITSUBISHI SEMICONDUCTOR <GaAs FET>

MGF1953A

Microwave Power MES FET (Leadless Ceramic Package)

DESCRIPTION

The MGF1953A is designed for use in S to Ku band power amplifiers.

The lead-less ceramic package assures minimum parasitic losses.

FEATURES

High gain and High P1dB

Glp=6.0dB, P1dB=20dBm (Typ.) @ f=12GHz

APPLICATION

S to Ku band power Amplifiers

QUALITY GRADE

GG

RECOMMENDED BIAS CONDITION

 $V_{DS}=6V$, $I_{D}=100mA$

ORDERING INFORMATION

Tape & reel 3000pcs./reel

Outline Drawing

Fig.1

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

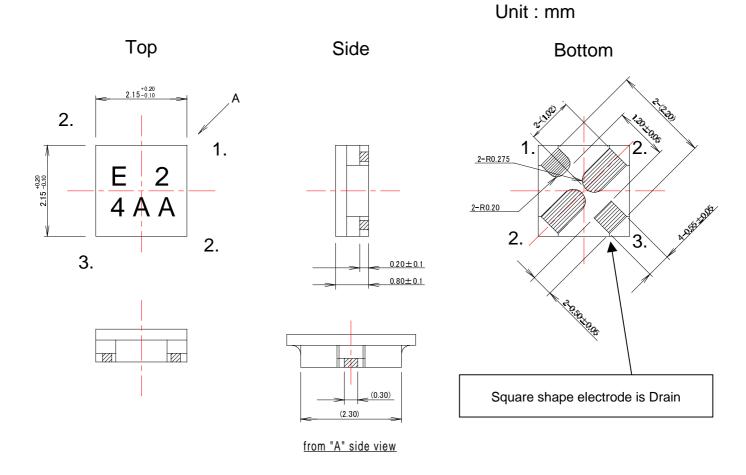
Symbol	Parameter	Ratings	Unit
V _{GDO}	Gate to drain voltage	-10	V
V _{GSO}	Gate to source voltage	-10	V
I _D	Drain current	400	mA
PT	Total power dissipation	1	W
T _{ch}	Channel temperature	125	°C
T _{stg}	Storage temperature	-65 to +125	°C

Keep Safety first in your circuit designs! Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measure such as (I) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Synbol	Parameter	Test conditions	Limits			Unit
			MIN.	TYP.	MAX	
V(BR)GDO	Gate to drain breakdown voltage	Ig=-100μA	-10	-15		V
I _{DSS}	Saturated drain current	V _{GS} =0V,V _{DS} =3V	105	200	400	mA
V _{GS(off)}	Gate to source cut-off voltage	V _{DS} =3V,I _D =1mA	-0.3	-1.4	-3.5	V
P1dB	Output Power at 1dB gain	V _{DS} =4V,ID=100mA	18	20		dBm
	Compression	f=12GHz				
Glp	Linear Power Gain	V _{DS} =4V,ID=100mA	4	6		dB
		f=12GHz,Pin=5dBm				

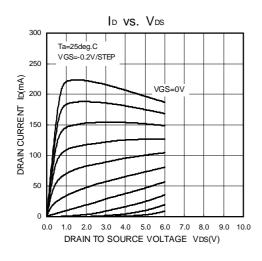
Fig.1

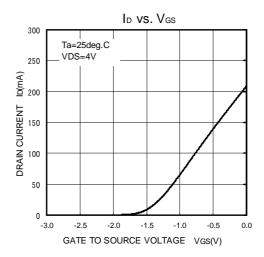


- 1. Gate
- 2. Source
- 3. Drain

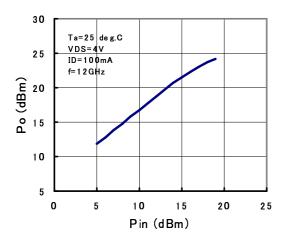
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TYPICAL CHARACTERISTICS (Ta=25°C)





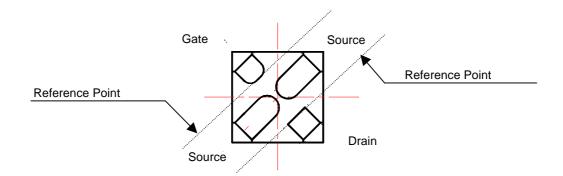
Po vs. Pin



S PARAMETERS

(Conditions: VDS=4V,ID=100mA,Ta=25deg.C)

f	S11		S	S21 S		S12 S		22	K	MAG/MSG
(GHz)	Mag.	Angle	Mag.	Angle	Mag.	Angle	Mag.	Angle		(dB)
1	0.907	-51.1	8.288	143.0	0.026	63.3	0.148	-62.0	0.40	25.0
2	0.775	-95.1	6.461	112.7	0.041	42.5	0.161	-105.9	0.73	21.9
3	0.702	-121.5	5.090	95.3	0.049	34.4	0.173	-123.3	0.99	20.1
4	0.674	-144.5	4.128	79.9	0.055	28.9	0.187	-138.9	1.16	16.3
5	0.661	-161.3	3.521	66.9	0.060	23.7	0.190	-145.1	1.29	14.5
6	0.653	-175.4	3.105	54.6	0.065	20.8	0.185	-146.9	1.38	13.1
7	0.650	170.8	2.810	41.7	0.071	17.5	0.175	-147.3	1.41	12.2
8	0.650	157.4	2.609	28.9	0.078	12.7	0.164	-149.1	1.40	11.5
9	0.642	143.3	2.440	16.2	0.086	6.9	0.142	-154.0	1.40	10.8
10	0.640	127.4	2.270	2.4	0.096	-0.1	0.114	-165.1	1.39	10.0
11	0.623	109.0	2.091	-12.5	0.103	-10.3	0.083	166.0	1.50	8.9
12	0.619	90.0	1.908	-27.6	0.106	-20.4	0.085	113.6	1.63	7.9
13	0.634	71.7	1.710	-42.4	0.108	-29.8	0.140	75.8	1.75	7.0
14	0.666	54.3	1.507	-57.2	0.107	-41.2	0.217	54.5	1.86	6.2
15	0.713	39.4	1.314	-70.2	0.105	-50.7	0.300	41.8	1.89	5.5
16	0.769	27.0	1.139	-82.8	0.101	-59.9	0.378	32.0	1.84	5.2
17	0.822	15.6	0.976	-95.2	0.097	-68.4	0.455	23.4	1.76	5.0
18	0.865	5.9	0.821	-107.2	0.091	-77.2	0.513	15.3	1.67	4.7



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